Atty Docket: ASMMC.047AUS

Deposit gate oxide

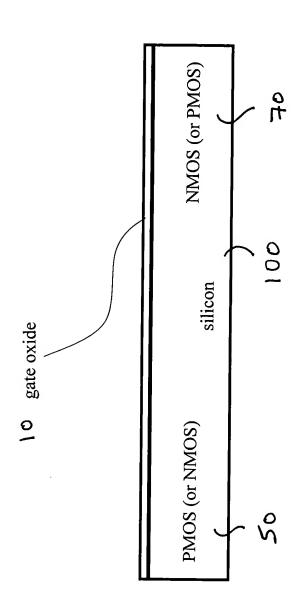
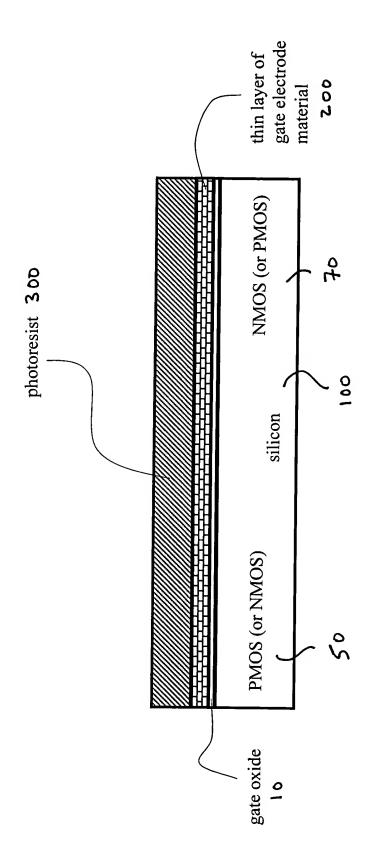


FIG.

thin layer of gate electrode material 200 NMOS (or PMOS) 40 001 silicon PMOS (or NMOS) 20 gate oxide

Deposit thin layer of gate electrode material

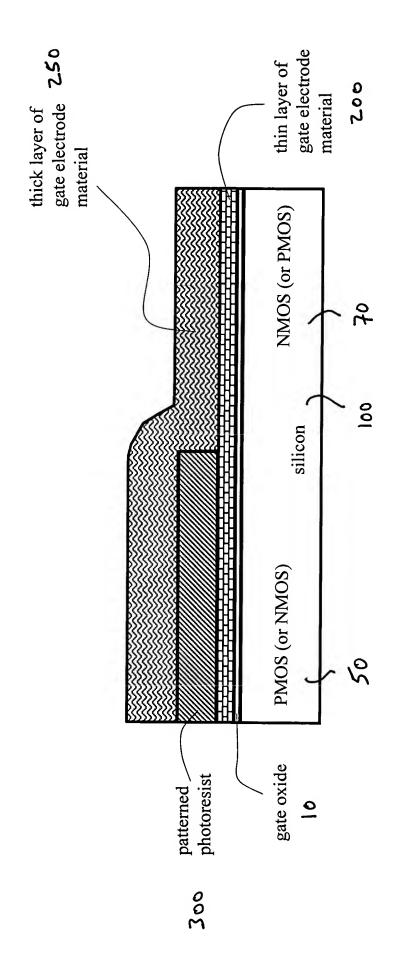


Deposit photoresist

gate electrode material thin layer of NMOS (or PMOS) 40 patterned photoresist 300 000 silicon PMOS (or NMOS) 20 gate oxide

Pattern and etch photoresist

FIG. 4



Deposit thick layer of gate electrode material

FIG. 5

Chemical mechanical polishing (CMP)

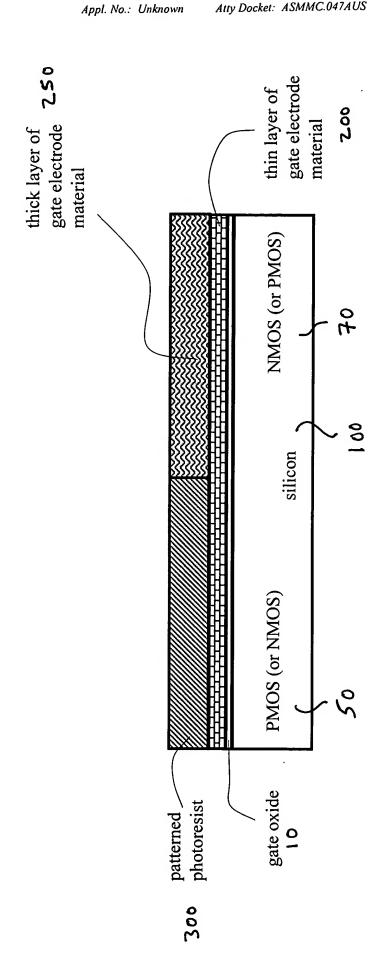
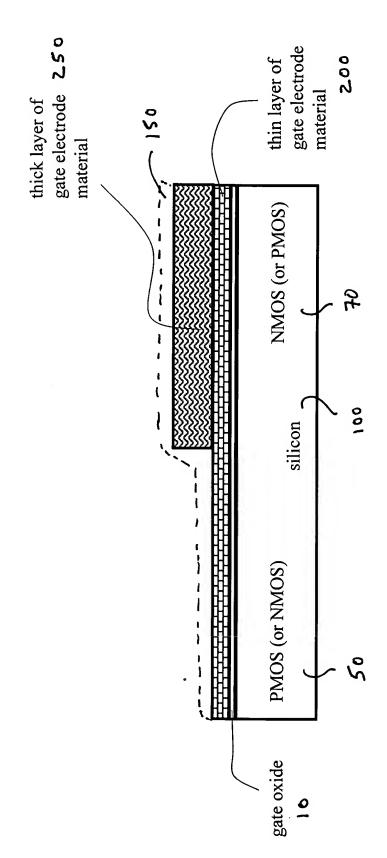
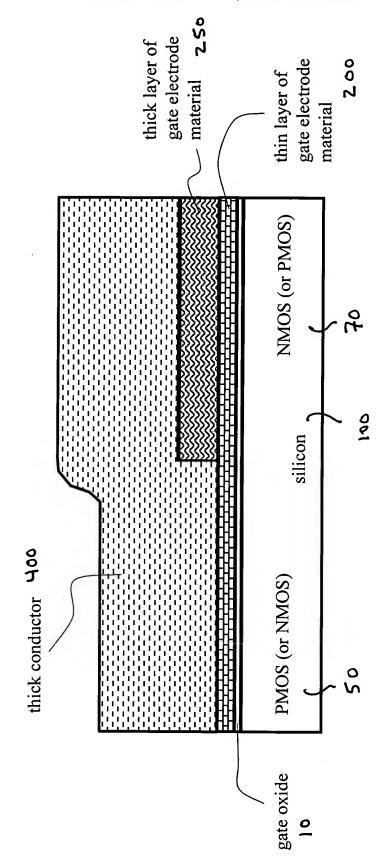


FIG. 6



Etch photoresist

FIG. 7



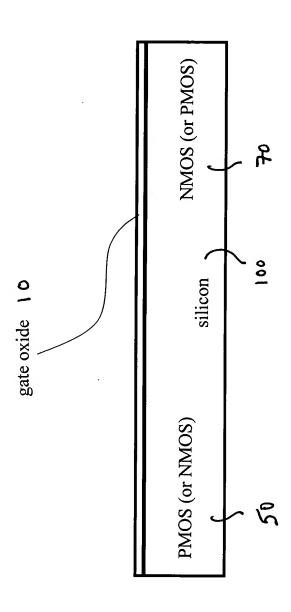
Deposit thick conductor, such as poly-Si, W, Al, Ni, Ru, RuO<sub>2</sub>

FIG. 8

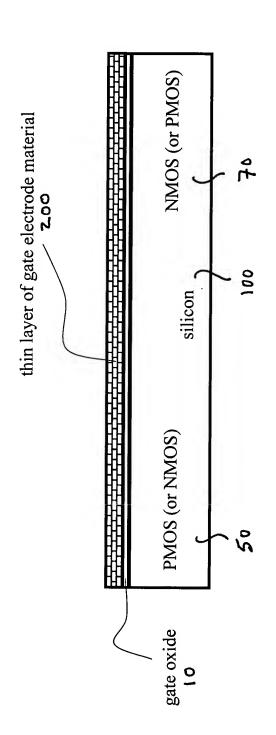
gate electrode thick layer of 200 gate electrode thin layer of material material NMOS (or PMOS) 70 <u>8</u> silicon thick conductor 400 PMOS (or NMOS) gate oxide

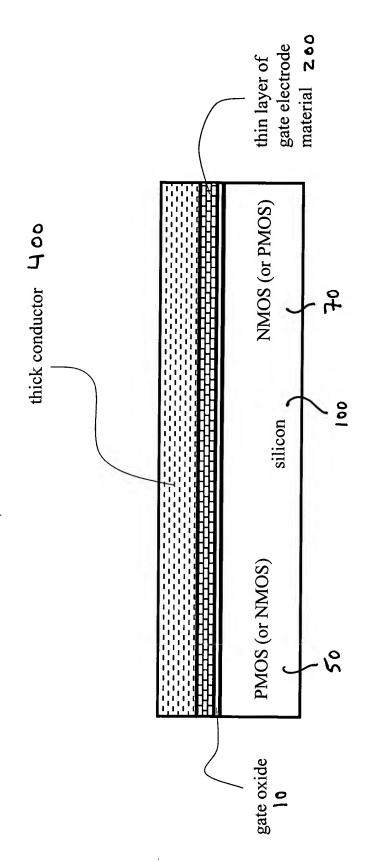
Chemical mechanical polishing (CMP)

Deposit gate oxide



Deposit thin layer of gate electrode material





Deposit thick conductor

gate electrode material 200 thick 400 conductor thin layer of NMOS (or PMOS) 300 photoresist 001 silicon PMOS (or NMOS) gate oxide

Deposit photoresist

200 gate electrode material 200 thin layer of NMOS (or PMOS) 40 Pattern and etch thick conductor 100 silicon photoresist | 300 PMOS (or NMOS) 20 gate oxide thick conductor? 400



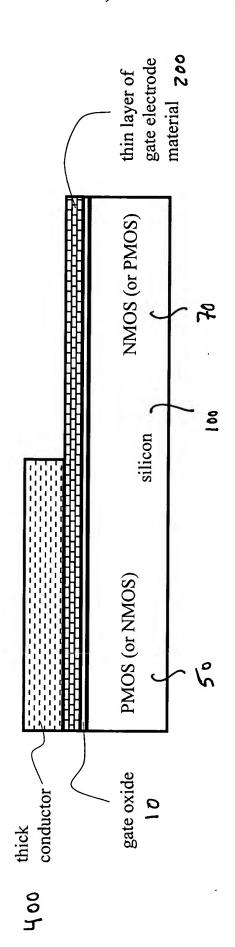
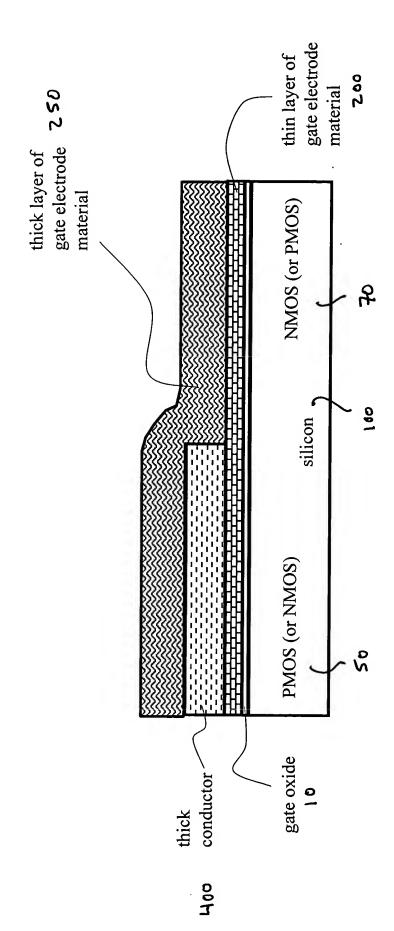


FIG. 14



Deposit thick gate electrode

FIG. 16

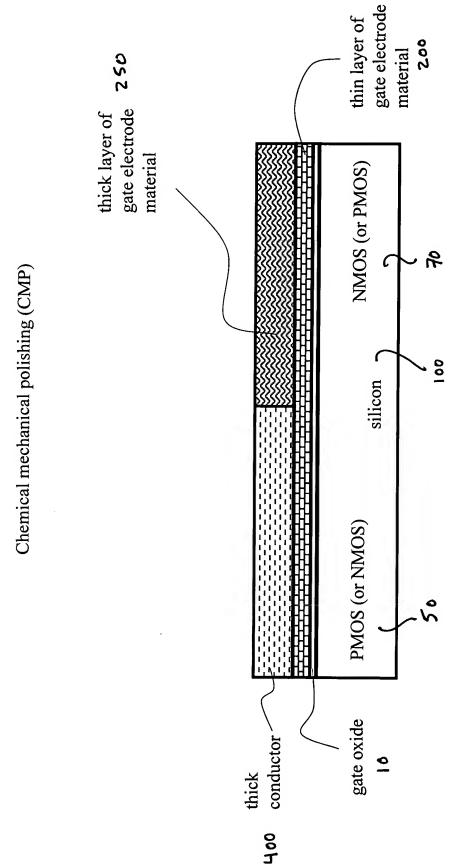
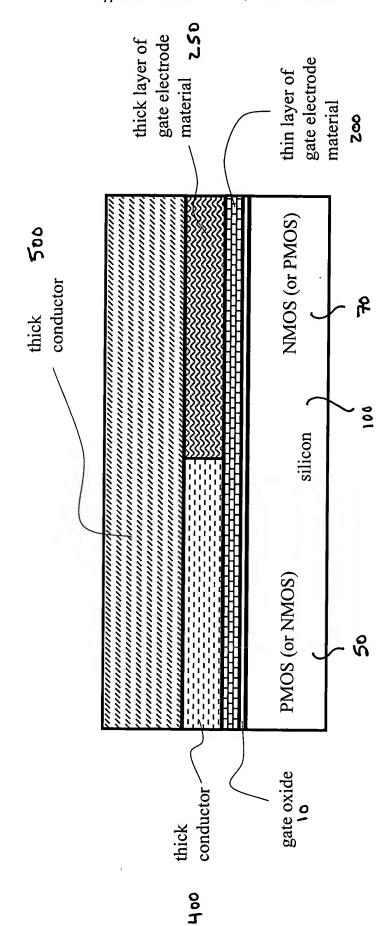


FIG. 1

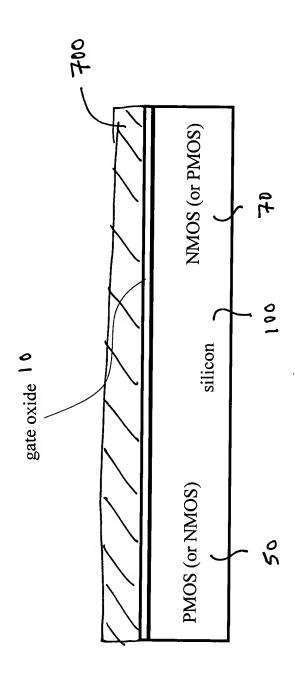
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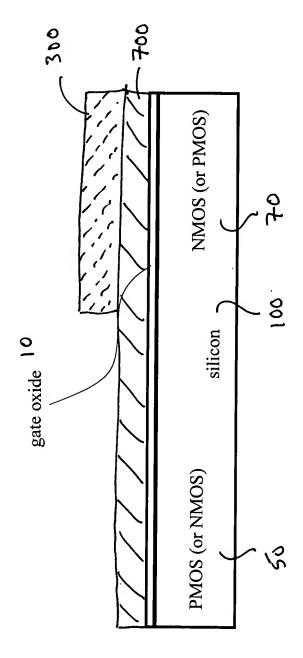


Deposit thick conductor

IG. 13

Deposit gate oxide





Deposit gate oxide

FIG. Lo

Deposit gate oxide

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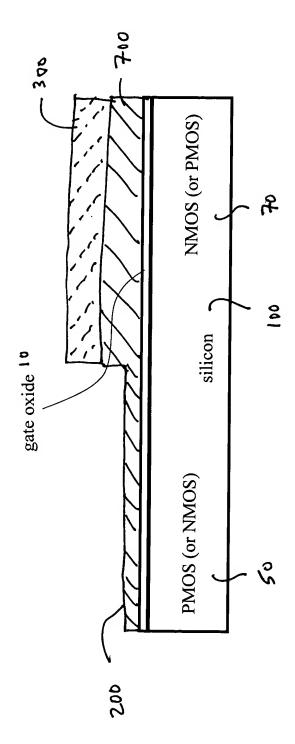


FIG.

Deposit gate oxide

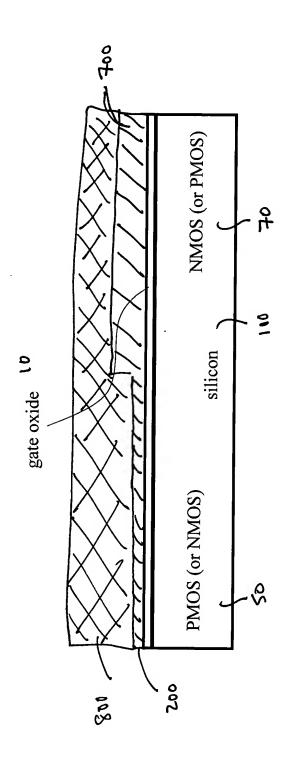


FIG. 12